

Device Characteristics

Parameter	Condition	Min	Typ	Max	Unit
Diameter		-	500	-	μm
Wavelength Range		400	-	1000	nm
Peak Sensitivity		-	800	-	nm
Voltage Breakdown Temp Coefficient	$I_D = 10\mu A$	-	0.5	-	V/°C
Capacitance	V_{OP}	-	2	-	pF
Rise Time	V_{OP}	-	300	-	psec
Noise Current	V_{OP}	-	200	-	fA/rt(Hz)

Measured Characteristics

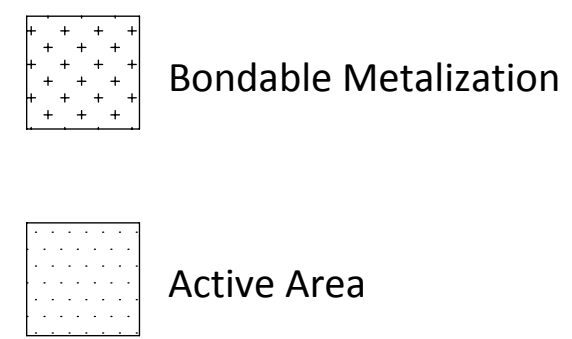
Parameter	Condition	Min	Typ	Max	Unit
Breakdown Voltage	$I_D = 10\mu A$	-	150	200	V
Peak Responsivity	$V_{OP}; 905nm$	-	50	-	A/W
Dark Current	V_{OP}	-	1	3	nA

$T_A = 25^\circ C$ unless indicated otherwise

V_{OP} @ $M = 100$

Absolute Maximum Ratings

Parameter	Min	Max	Unit
Storage Temperature	-55	100	°C
Operating Temperature	-20	60	
Soldering (15s)	-	260	mA
Reverse Current (Peak)	CW	0.200	
	1s Pulse	1	
Forward Current (Avg)	CW	10	
	1s Pulse	50	
Max Total Power Dissipation	-	60	mW



REV.	DESCRIPTION	DATE	REVISED BY
	REVISIONS		

Drawn By: *[Signature]*
 On: 7/20/2015
 Drafting: *[Signature]*
 Engineering: *[Signature]*
 Production: *[Signature]*
 Management: *[Signature]*



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UNLESS OTHERWISE SPECIFIED:
 DIMENSIONS ARE IN MM [INCH]

STANDARD TOLERANCES - METRIC:
 ANGULAR: ±5°
 ONE PLACE DECIMAL: ±0.5
 TWO PLACE DECIMAL: ±0.1

TITLE: Epitaxial Silicon APD
 ∅500μm Active Area
 High-Speed
 Chip Layout

SIZE	DWG. NO.	REV
B	C-SAH500HD	

SCALE: 70:1 SHEET 1 OF 1